

0.8A, 200V - 600V Miniature Glass Passivated Fast Recovery Surface Mount Bridge Rectifier

FEATURES

- Ideal for automated placement
- Reliable low cost construction utilizing molded plastic technique
- High surge current capability
- Small size, simple installation
- UL Recognized File # E-326243
- Moisture sensitivity level: level 1, per J-STD-020
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

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- Switching mode power supply (SMPS)
- Lighting application

MECHANICAL DATA

- Case: TO-269AA (MBS)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.12g (approximately)

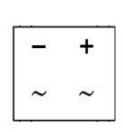
KEY PARAMETERS						
PARAMETER	VALUE	UNIT				
I _{F(AV)}	0.8	Α				
V_{RRM}	200 - 600	V				
I _{FSM}	30	Α				
T_{JMAX}	150	°C				
Package	TO-269AA (MBS)					
Configuration	Quad					

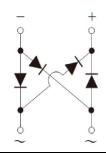






TO-269AA (MBS)





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)							
PARAMETER	SYMBOL	RMB2S	RMB4S	RMB6S	UNIT		
Marking code on the device		RMB2S	RMB4S	RMB6S			
Repetitive peak reverse voltage	V_{RRM}	200	400	600	V		
Reverse voltage, total rms value	$V_{R(RMS)}$	140	280	420	V		
Maximum DC blocking voltage	V_{DC}	200	400	600	V		
Maximum average forward current 60Hz sine wave resistance load on glass-epoxy P.C.B.	ı	0.5			А		
Maximum average forward current 60Hz sine wave resistance load on aluminum substrate	I _{F(AV)}		0.8		А		
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}		30		А		
Rating for fusing (t<8.3ms)	I ² t	3.74		A ² s			
Junction temperature	T _J	- 55 to +150		°C			
Storage temperature	T _{STG}	- 55 to +150		°C			



THERMAL PERFORMANCE						
PARAMETER	SYMBOL	TYP	UNIT			
Junction-to-ambient thermal resistance per diode	$R_{\Theta JA}$	85	°C/W			

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	TYP	MAX	UNIT	
Forward voltage per diode (1)	I _F = 0.4A, T _J = 25°C	V _F	-	1	V	
	T _J = 25°C		-	5	μA	
Reverse current @ rated V _R per diode ⁽²⁾	T _J = 125°C	- I _R	-	100	μA	
Junction capacitance	1 MHz, V _R =4.0V	Сл	13	-	pF	
Reverse recovery time	I _F =0.5A,I _R =1.0A I _{RR} =0.25A	t _{rr}	-	150	ns	

Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms

ORDERING INFORMATION						
PART NO.	PART NO. SUFFIX(*)	PACKING CODE	PACKING CODE SUFFIX	PACKAGE	PACKING	
RMBxS		RC	0	MBS	3,000 / 13" Paper reel	
(Note 1, 2)	Н	MC	G		3,000 / 13" Plastic reel	

Notes:

- 1. "x" defines voltage from 200V (RMB2S) to 600V (RMB6S)
- 2. Whole series with green compound (halogen-free)
- *: Optional available

EXAMPLE						
EXAMPLE P/N	PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX	DESCRIPTION	
RMB2SHRCG	RMB2S	Н	RC	G	Green compound AEC-Q101 qualified	



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

1 AVERAGE FORWARD CURRENT (A) 0.8 Aluminum Substrate 0.6 0.4 Glass Epoxy P.C.B. 0.2 0 0 20 40 60 80 100 120 140 160 AMBIENT TEMPERATURE (°C)

Fig.2 Typical Junction Capacitance

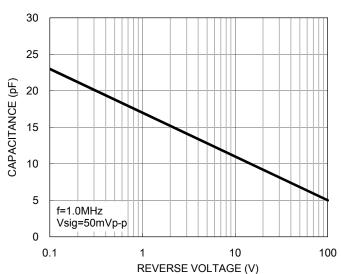


Fig.3 Typical Reverse Characteristics

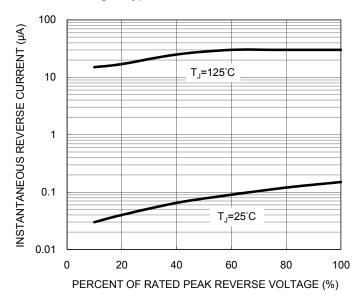
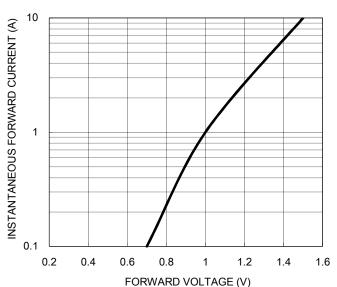


Fig.4 Typical Forward Characteristics





CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.5 Maximum Non-repetitive Forward Surge Current

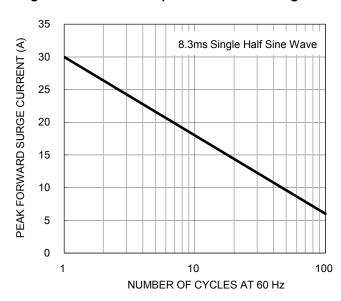
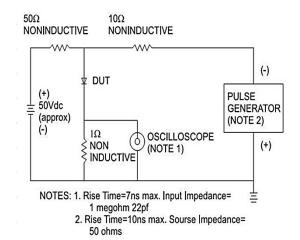
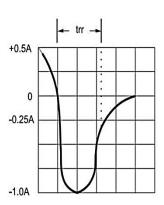


Fig.6 Reverse Recovery Time Characteristic and Test Circuit Diagram



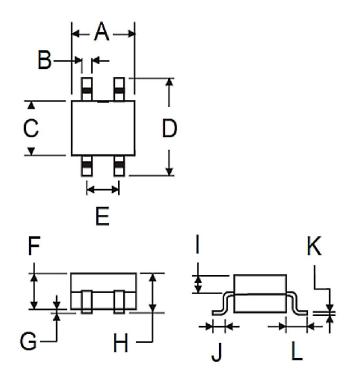


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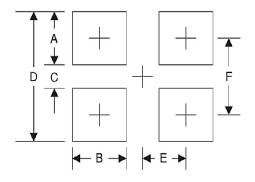
PACKAGE OUTLINE DIMENSIONS

TO-269AA (MBS)



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DIM.	Unit	(mm)	Unit (inch)		
DIWI.	Min	Max	Min	Max	
Α	4.50	4.90	0.177	0.193	
В	0.56	0.84	0.022	0.033	
С	3.60	5.00	0.142	0.197	
D	-	6.90	-	0.272	
Е	2.20	2.60	0.087	0.102	
F	2.30	2.70	0.091	0.106	
G	-	0.20	-	0.008	
Н	-	2.90	-	0.114	
I	0.95	1.53	0.037	0.060	
J	0.70	1.10	0.028	0.043	
K	0.15	0.35	0.006	0.014	
L	1.10	2.12	0.043	0.083	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
А	1.70	0.067
В	0.90	0.035
С	4.40	0.173
D	8.10	0.319
E	1.30	0.051
F	6.30	0.248

MARKING DIAGRAM



P/N = Marking Code YW = Date Code F = Factory Code



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